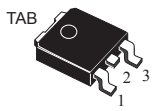
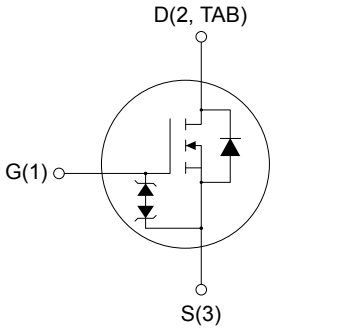
STD13N50DM2AG

Datasheet

Automotive-grade N-channel 500 V, 320 mΩ typ., 11 A MDmesh DM2 Power MOSFET in a DPAK package



DPAK



NG1D2TS3Z

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STD13N50DM2AG	500 V	360 mΩ	11 A

- AEC-Q101 qualified
- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Product status
STD13N50DM2AG

Product summary	
Order code	STD13N50DM2AG
Marking	13N50DM2
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	11	A
I_D	Drain current (continuous) at T_C= 100 °C	8	
I_{DM} (1)	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at T_C = 25 °C	110	W
dv/dt (2)	Peak diode recovery voltage slope	50	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 11 A, di/dt ≤ 800 A/µs; $V_{DS\ peak}$ < $V_{(BR)DSS}$, V_{DD} = 400 V*
3. *V_{DS} ≤ 400 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.14	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	50	

1. *When mounted on a 1-inch² FR-4, 2 oz Cu board*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetetive or not repetetive (pulse width limited by T_{jmax})	2	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	230	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified).

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	500			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 500 V			1	µA
		V_{GS} = 0 V, V_{DS} = 500 V, T_C = 125 °C(1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 5.5 A		320	360	mΩ

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 100 V, f = 1 MHz, V_{GS} = 0 V	-	597	-	pF
C_{oss}	Output capacitance		-	38	-	pF
C_{rss}	Reverse transfer capacitance		-	3.5	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	-	69	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 400 V, I_D = 11 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	11.7	-	nC
Q_{gs}	Gate-source charge		-	3.8	-	nC
Q_{gd}	Gate-drain charge		-	4.2	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 250 V, I_D = 5.5 A R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	13	-	ns
t_r	Rise time		-	9	-	ns
$t_{d(off)}$	Turn-off delay time		-	26	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		11	A
I_{SDM} (1)	Source-drain current (pulsed)		-		28	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 11 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 11 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	68		ns
Q_{rr}	Reverse recovery charge		-	200		nC
I_{RRM}	Reverse recovery current		-	5.9		A
t_{rr}	Reverse recovery time	I_{SD} = 11 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	107		ns
Q_{rr}	Reverse recovery charge		-	450		nC
I_{RRM}	Reverse recovery current		-	8.5		A

1. *Pulse width is limited by safe operating area*
2. *Pulse test: pulse duration = 300 µs, duty cycle 1.5%*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

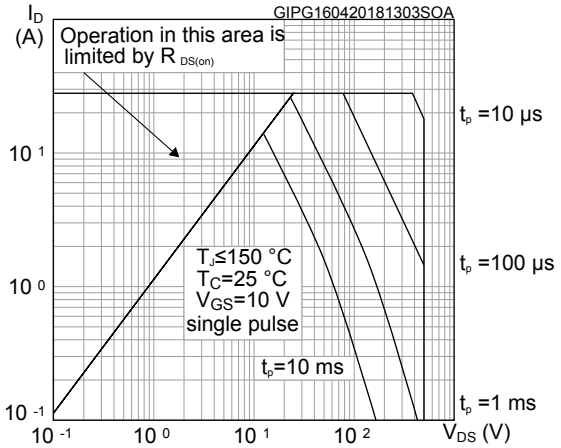


Figure 2. Normalized transient thermal impedance

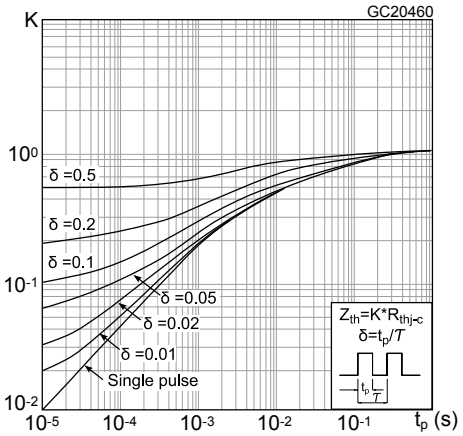


Figure 3. Typical output characteristics

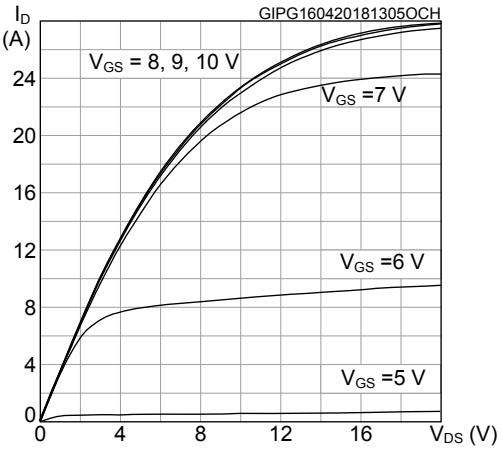


Figure 4. Typical transfer characteristics

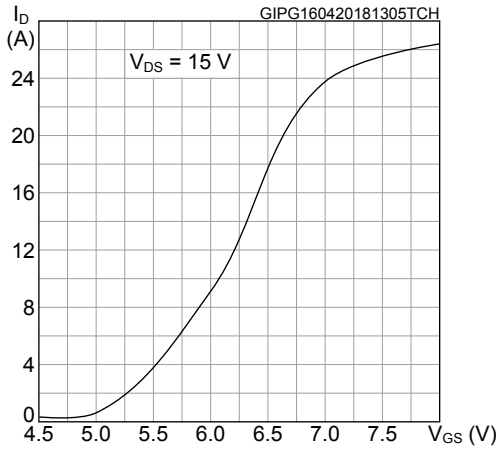


Figure 5. Normalized gate threshold vs temperature

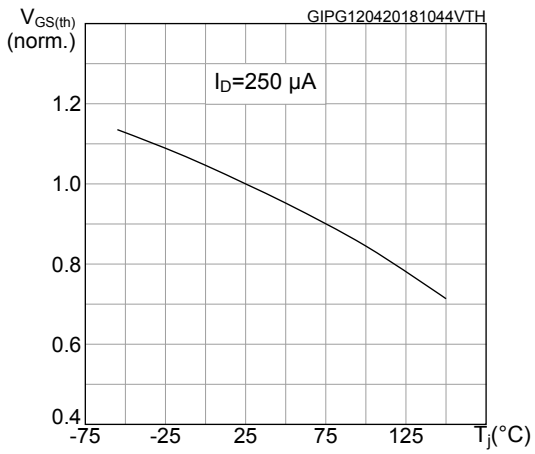


Figure 6. Normalized breakdown voltage vs temperature

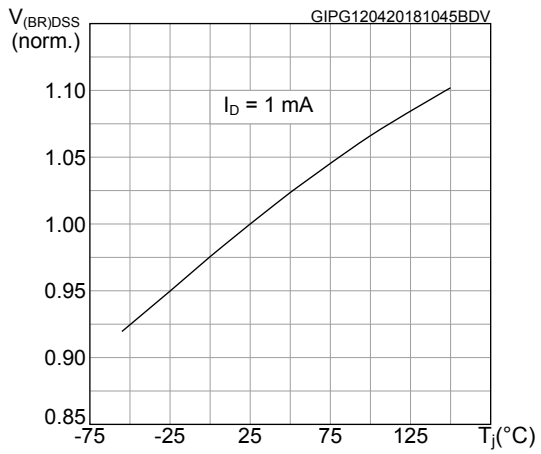


Figure 7. Typical drain-source on-resistance

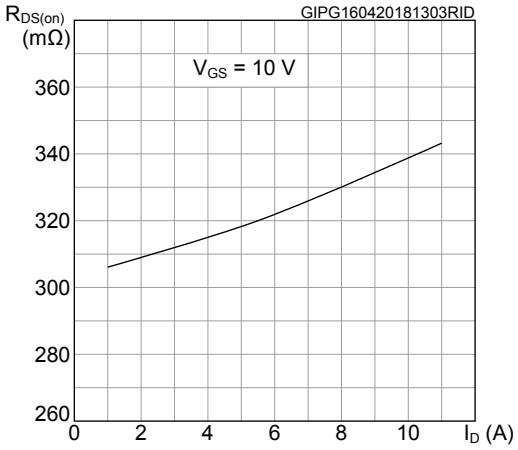


Figure 8. Normalized on-resistance vs. temperature

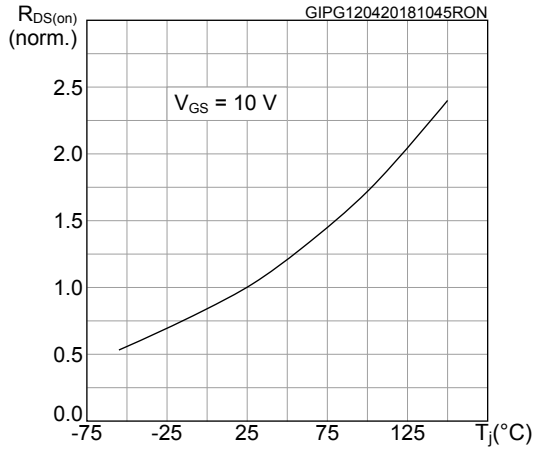


Figure 9. Typical gate charge characteristics

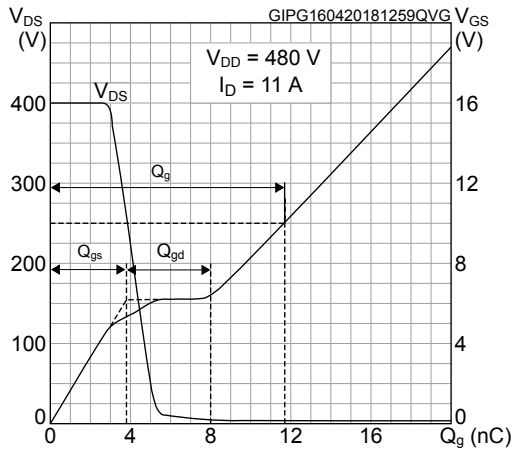


Figure 10. Typical capacitance characteristics

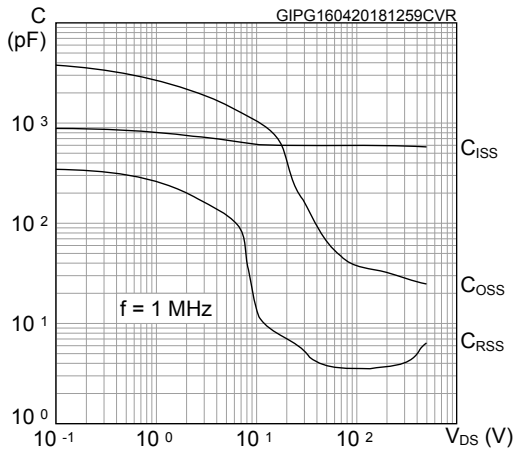


Figure 11. Typical output capacitance stored energy

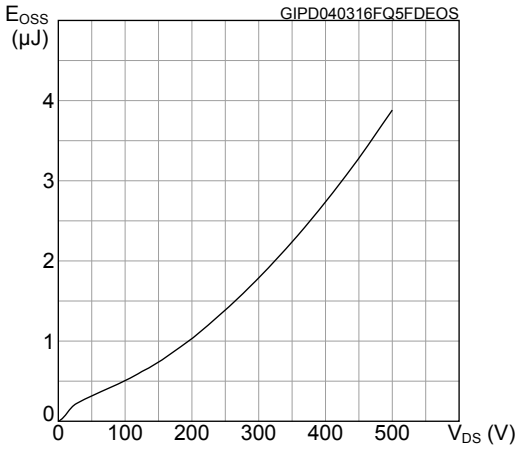
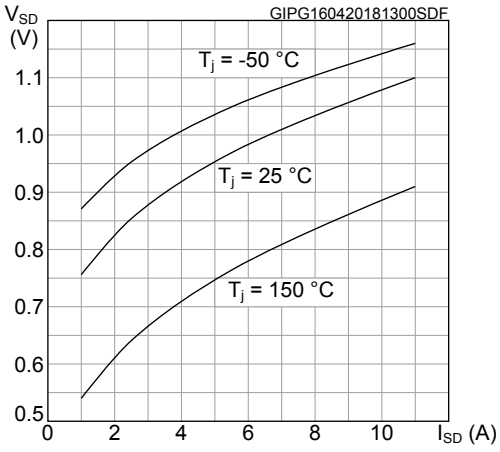


Figure 12. Typical reverse diode forward characteristics



3 Test circuits

Figure 13. Test circuit for resistive load switching times

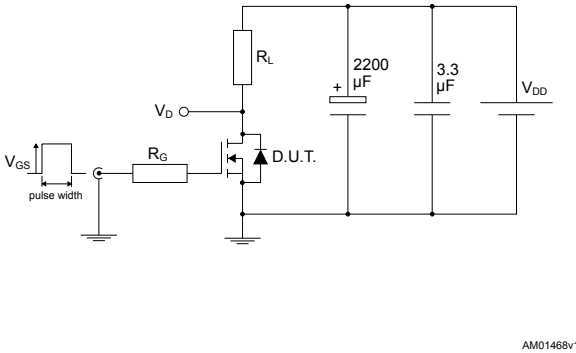


Figure 14. Test circuit for gate charge behavior

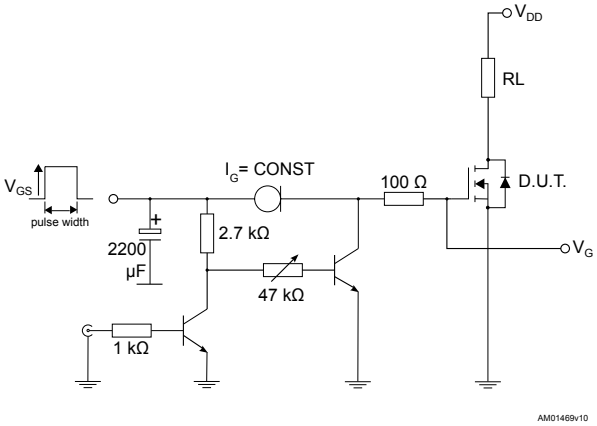


Figure 15. Test circuit for inductive load switching and diode recovery times

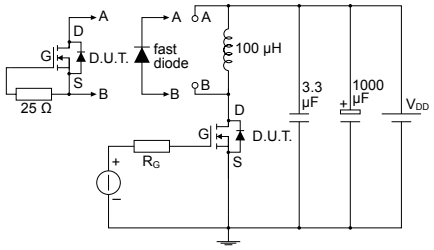


Figure 16. Unclamped inductive load test circuit

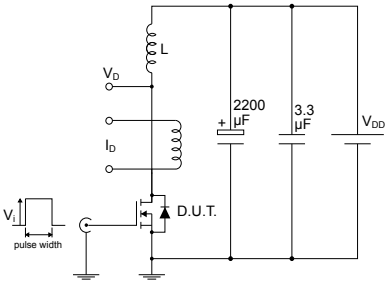


Figure 17. Unclamped inductive waveform

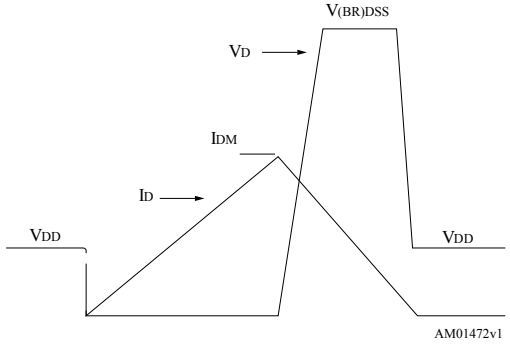
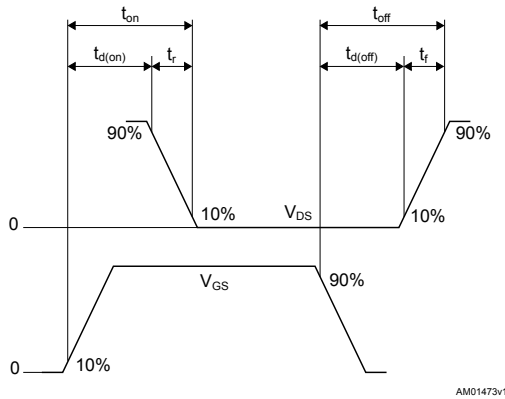


Figure 18. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 19. **DPAK (TO-252) type A2 package outline**

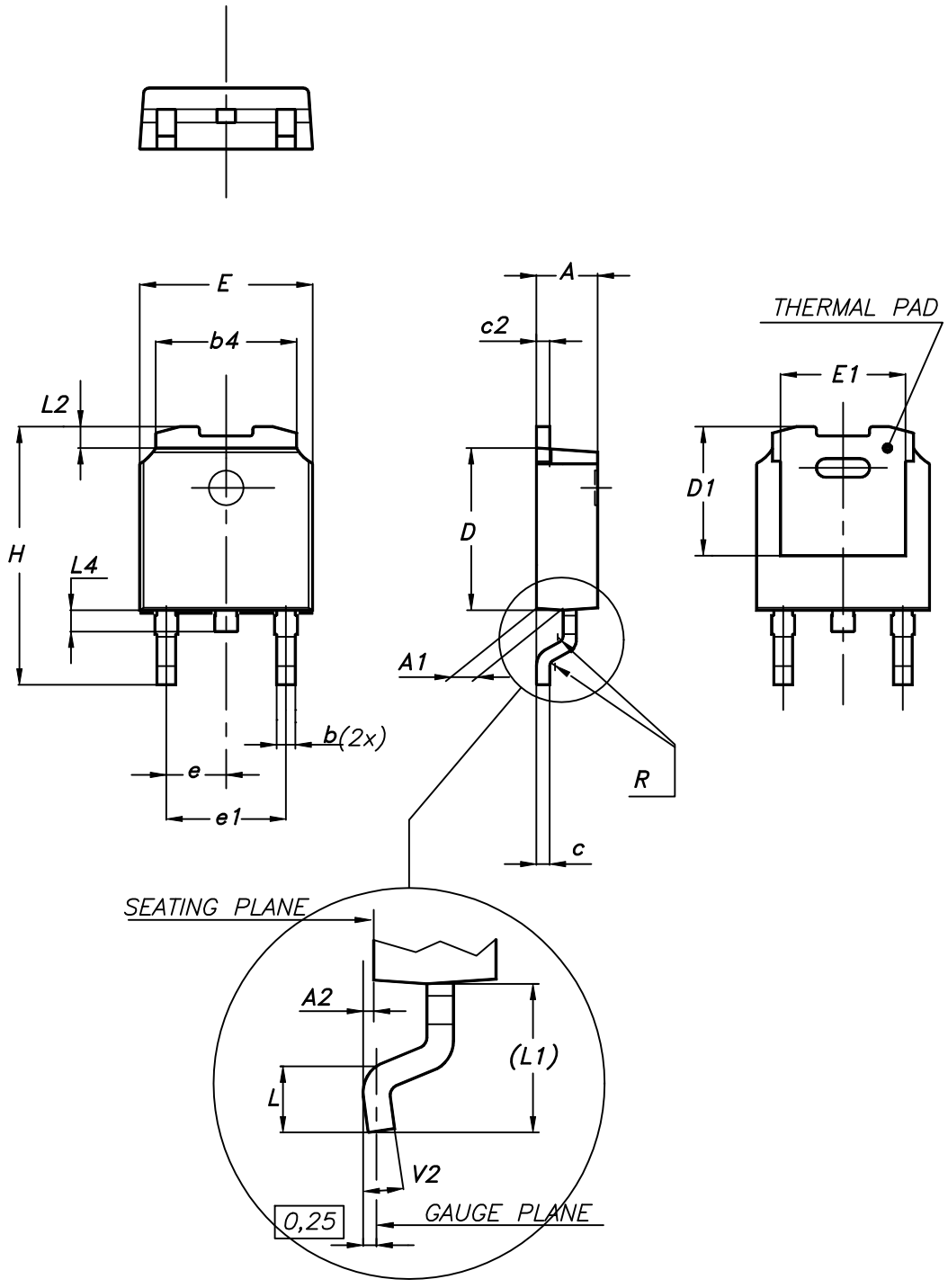
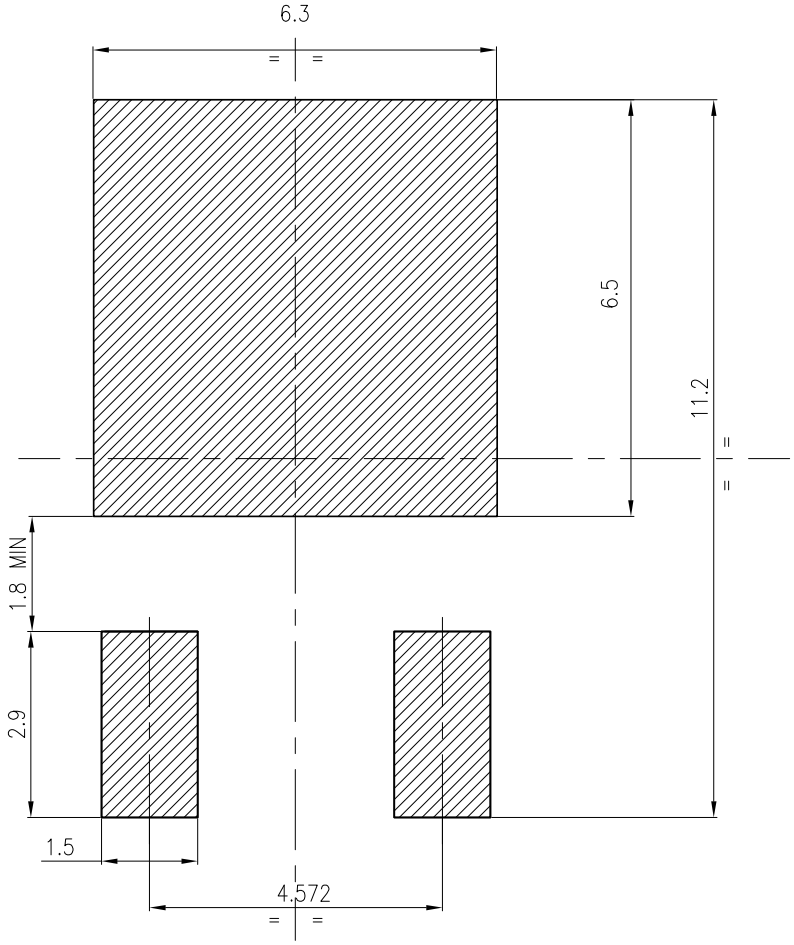


Table 8. **DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20. **DPAK (TO-252) recommended footprint (dimensions are in mm)**



4.2 DPAK (TO-252) packing information

Figure 21. **DPAK (TO-252) tape outline**

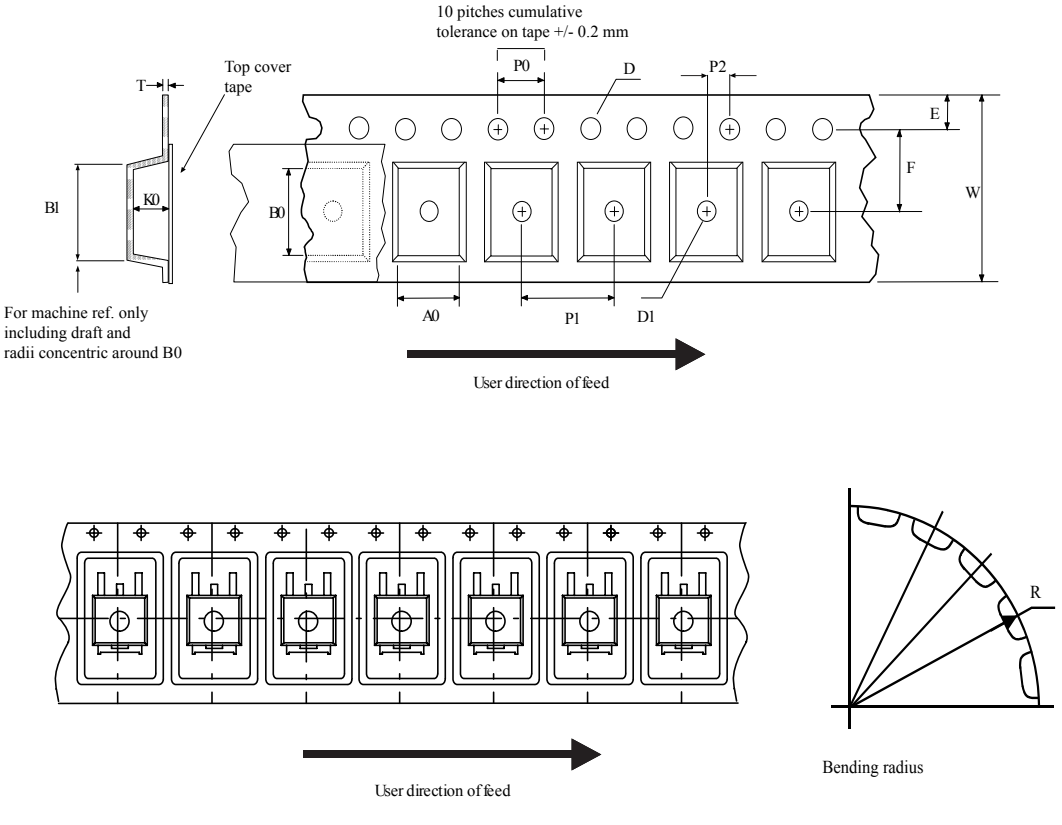


Figure 22. **DPAK (TO-252) reel outline**

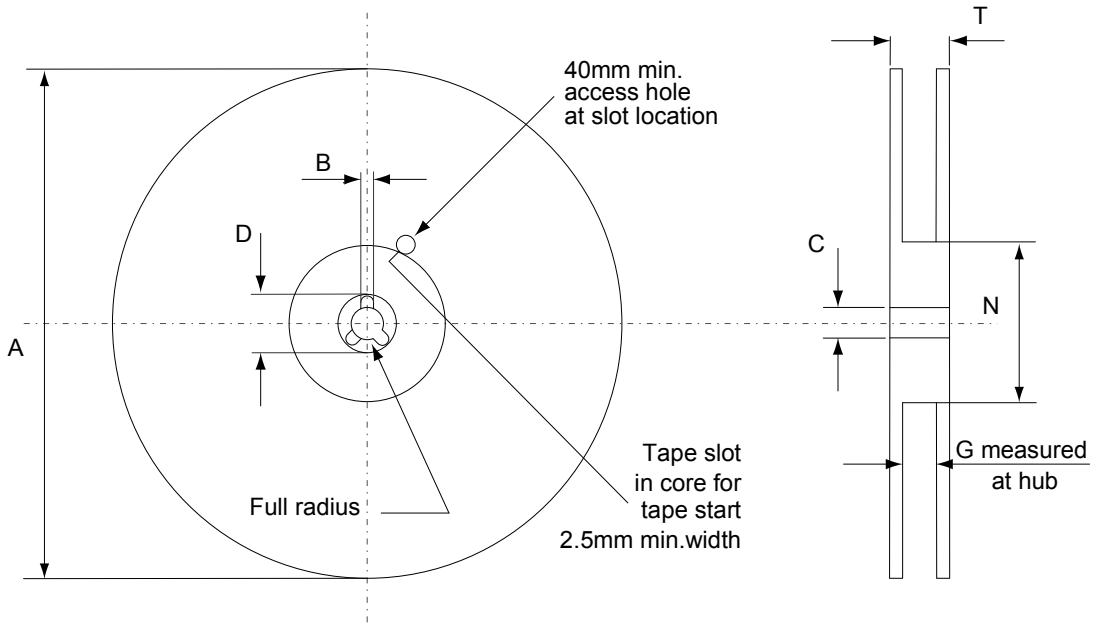


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Table 9. **DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 10. **Document revision history**

Date	Revision	Changes
23-Jun-2017	1	First release.
16-Apr-2018	2	Removed maturity status indication from cover page. The document status is production data. Modified title, *Table 1. Absolute maximum ratings*, *Table 3. Avalanche characteristics*, *Table 4. Static*, *Table 5. Dynamic*, *Table 6. Switching times*, *Table 7. Source drain diode*. Modified *Section 2.1 Electrical characteristics (curves).* Minor text changes.
27-Jun-2018	3	Updated *Section 4 Package information.*
31-Oct-2019	4	Modified Features table on cover page and Table 4. Static. Updated Section 4.1 DPAK (TO-252) type A2 package information. Minor text changes.

Contents